



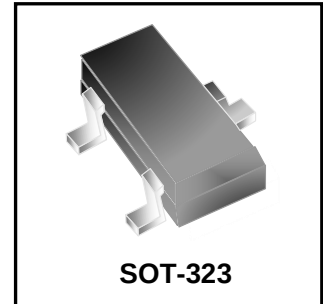
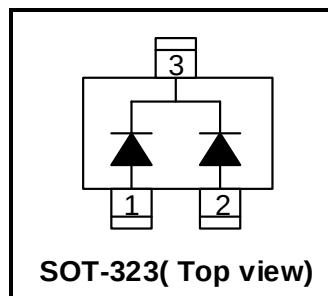
WSR4002W2

Schottky Barrier Diode

Features

- Low Forward Voltage Schottky Rectifier
- High Conductance
- Low Current Leakage
- RoHS Compliant / Green EMC

Schematic & PIN Configuration



Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	40	V
Working peak reverse voltage	V_{RWM}	40	V
DC blocking voltage	V_R	40	V
Forward Continuous Current	I_F	200	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	667	°C/W
Junction Temperature	T_J	125	°C
Storage Temperature	T_{stg}	-55 to 150	°C

Electrical Characteristics ($T_{amb}=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_{BR}	$I_R = 10\mu\text{A}$	40	-	-	V
Reverse Voltage Leakage Current	I_R	$V_R = 30\text{V}$	-	-	200	nA
Forward Voltage	V_F	$I_F = 1\text{mA}$	-	-	0.38	V
		$I_F = 40\text{mA}$	-	-	1	
Diode Capacitance	C_D	$V_R = 0, f = 1\text{MHz}$	-	4.5	-	pF
Reverse Recovery Time	T_{rr}	$I_F = I_R = 10\text{mA}, I_{rr} = 1\text{mA}$ $R_L = 100\Omega$	-	4.5	-	ns

Typical Characteristics

Figure 1. Forward Characteristics

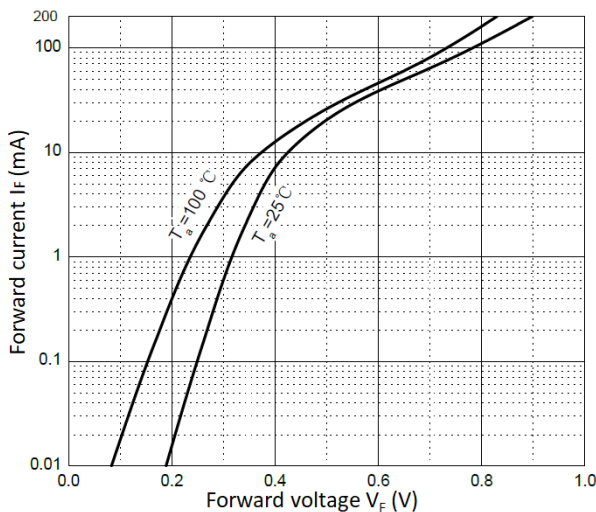


Figure 2. Reverse Characteristics

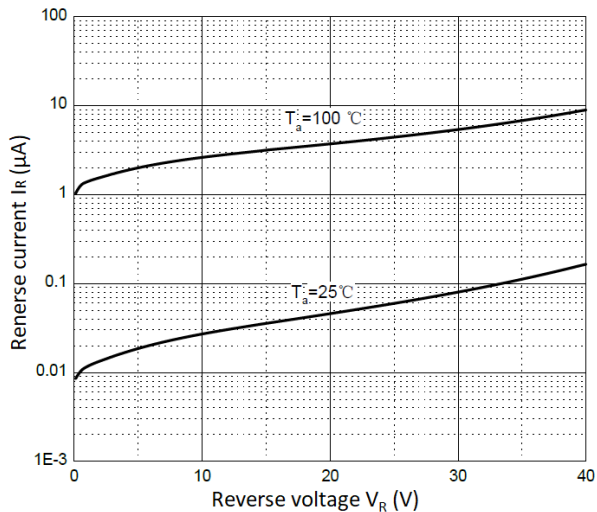


Figure 3. Capacitance Characteristics

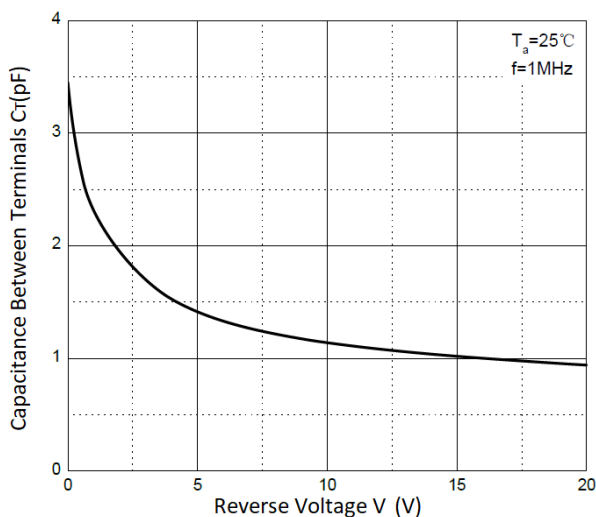
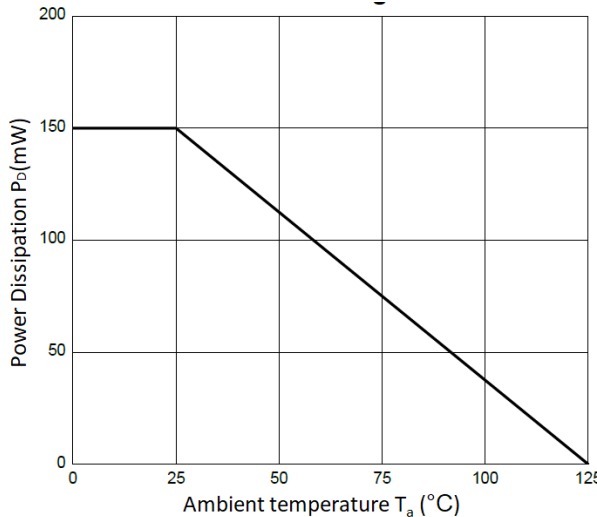
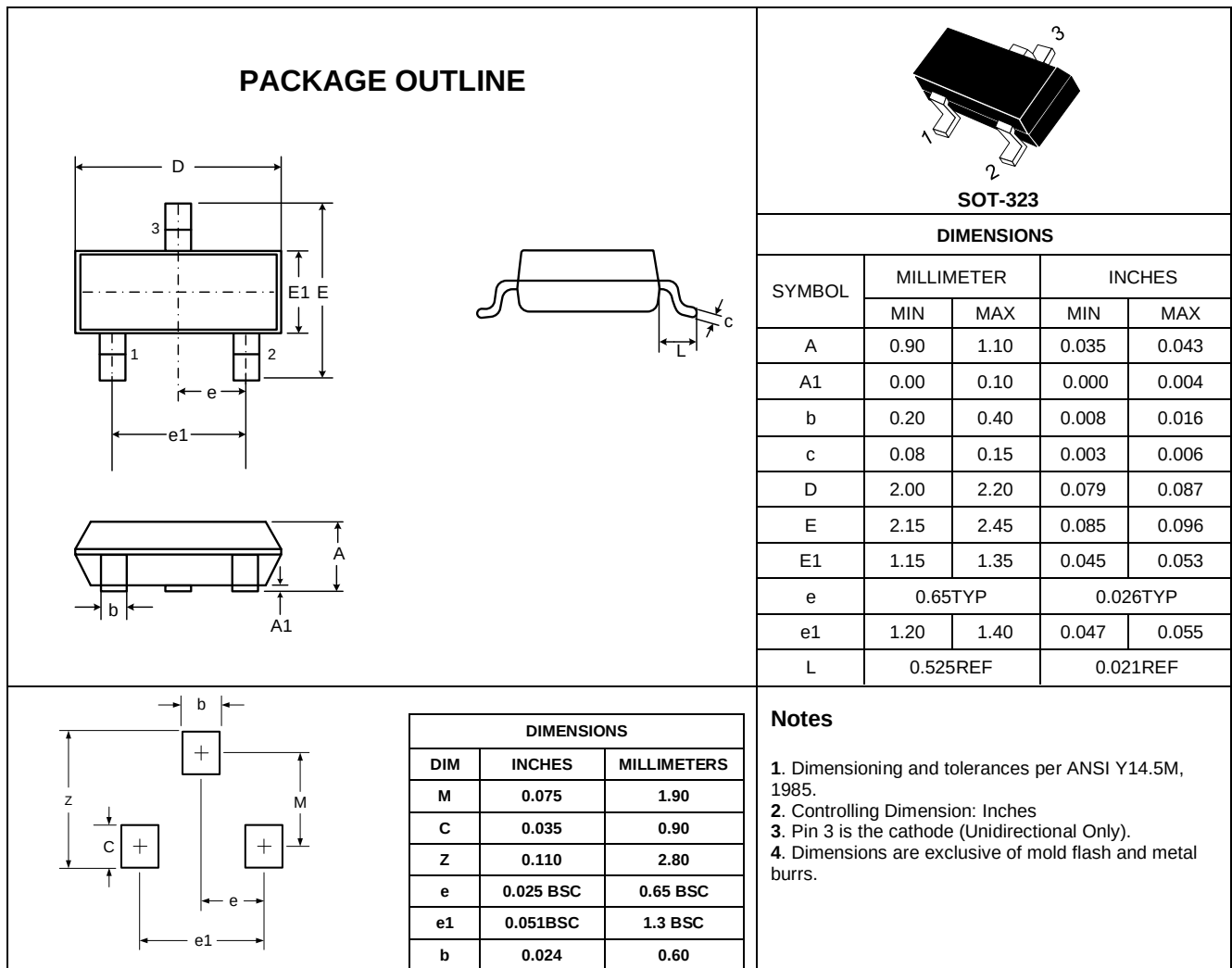


Figure 4. Power Derating Curve



Outline Drawing –SOT-323



Marking Codes

Part Number	WSR4002W2
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

No.1001, Shiwan (7) Road, Pudong District, Shanghai, P.R.China.201207

Tel: 86-21-68969993 Fax: 86-21-50757680 Email: market@way-on.comWAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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Specifications are subject to change without notice.
 The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
 Users should verify actual device performance in their specific applications.